

## FPN430 FPN430A



### PNP Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 2.0 A continuous. Sourced from Process PB.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	35	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	2.0	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

#### Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FPN430 / FPN430A	
P <sub>D</sub>	Total Device Dissipation	1.0	W
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	50	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	125	°C/W

**PNP Low Saturation Transistor**  
(continued)

**FPN430 / FPN430A**

**Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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**OFF CHARACTERISTICS**

BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0	30		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA, I <sub>E</sub> = 0	35		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 100 μA, I <sub>C</sub> = 0	5.0		V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0 V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0, T <sub>A</sub> = 100°C		100 10	nA μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4.0 V, I <sub>C</sub> = 0		100	nA

**ON CHARACTERISTICS\***

h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 2.0 V I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 2.0 V I <sub>C</sub> = 2.0 A, V <sub>CE</sub> = 2.0 V	<b>430</b> <b>430A</b>	100 250 60 40	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 100 mA I <sub>C</sub> = 2.0 A, I <sub>B</sub> = 200 mA	<b>430</b> <b>430A</b>	500 450 800	mV mV mV
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1.0 A, I <sub>B</sub> = 100 mA		1.25	V
V <sub>BE(on)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1.0 A, V <sub>CE</sub> = 2.0 V		1.0	V

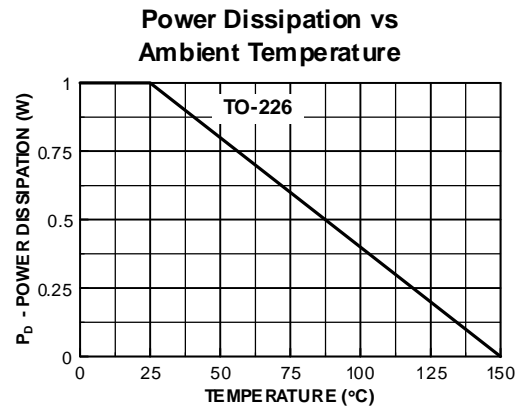
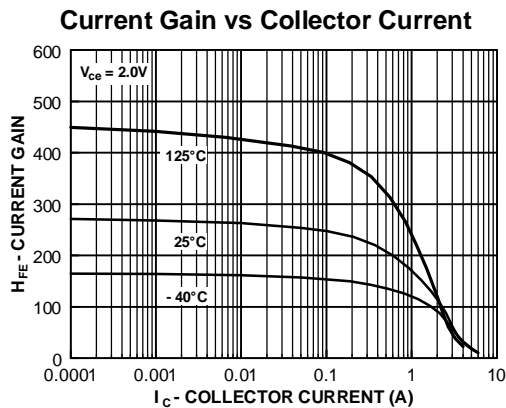
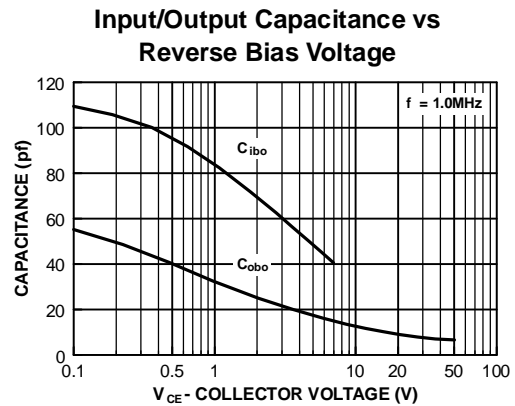
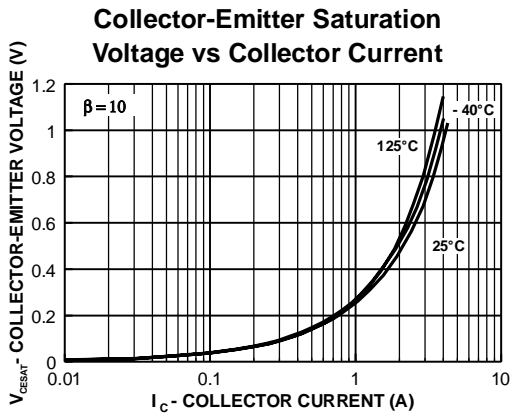
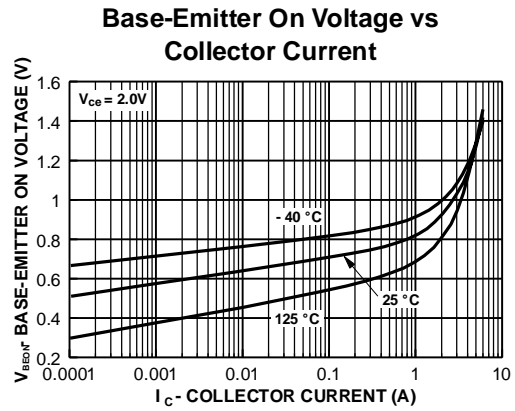
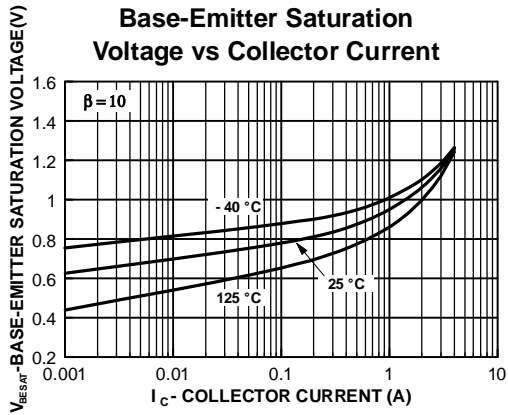
**SMALL SIGNAL CHARACTERISTICS**

C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		25	pF
F <sub>T</sub>	Transition Frequency	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 5.0 V, f = 100 MHz	100		MHz

\*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

**NOTE:** All voltages (V) and currents (A) are negative polarity for PNP transistors.

Typical Characteristics



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